

Semiconductor Devices Physics And Technology 2nd Edition

Market_Desc: · Electrical Engineers· Scientists Special Features: · Provides strong coverage of all key semiconductor devices. Includes basic physics and material properties of key semiconductors· Covers all important processing technologies About The Book: This book is an introduction to the physical principles of modern semiconductor devices and their advanced fabrication technology. It begins with a brief historical review of major devices and key technologies and is then divided into three sections: semiconductor material properties, physics of semiconductor devices and processing technology to fabricate these semiconductor devices.

Introduction to Semiconductor Device Physics is a popular and established text that offers a thorough introduction to the underlying physics of semiconductor devices. It begins with a review of basic solid state physics, then goes on to describe the properties of semiconductors including energy bands, the concept of effective mass, carrier concentration, and conduction in more detail. Thereafter the book is concerned with the principles of operation of specific devices, beginning with the Gunn Diode and the p-n junction. The remaining chapters cover the on specific devices, including the LED, the bipolar transistor, the field-effect transistor, and the semiconductor laser. The book concludes with a chapter providing a brief introduction to quantum theory. Not overtly mathematical, Introduction to Semiconductor Device Physics introduces only those physical concepts required for an understanding of the semiconductor devices being considered. The author's intuitive style, coupled with an extensive set of worked problems, make this the ideal introductory text for those concerned with understanding electrical and electronic engineering, applied physics, and related subjects.

Strain Effect in Semiconductors: Theory and Device Applications presents the fundamentals and applications of strain in semiconductors and semiconductor devices that is relevant for strain-enhanced advanced CMOS technology and strain-based piezoresistive MEMS transducers. Discusses relevant applications of strain while also focusing on the fundamental physics pertaining to bulk, planar, and scaled nano-devices. Hence, this book is relevant for current strained Si logic technology as well as for understanding the physics and scaling for future strained nano-scale devices.

Wide Bandgap Semiconductor Power Devices: Materials, Physics, Design and Applications provides readers with a single resource on why these devices are superior to existing silicon devices. The book lays the groundwork for an understanding of an array of applications and anticipated benefits in energy savings. Authored by the Founder of the Power Semiconductor Research Center at North Carolina State University (and creator of the IGBT device), Dr. B. Jayant Baliga is one of the highest regarded experts in the field. He thus leads this team who comprehensively review the materials, device physics, design considerations and relevant applications discussed. Comprehensively covers power

electronic devices, including materials (both gallium nitride and silicon carbide), physics, design considerations, and the most promising applications Addresses the key challenges towards the realization of wide bandgap power electronic devices, including materials defects, performance and reliability Provides the benefits of wide bandgap semiconductors, including opportunities for cost reduction and social impact

The main emphasis of this volume is on III-V semiconductor epitaxial and bulk crystal growth techniques. Chapters are also included on material characterization and ion implantation. In order to put these growth techniques into perspective a thorough review of the physics and technology of III-V devices is presented. This is the first book of its kind to discuss the theory of the various crystal growth techniques in relation to their advantages and limitations for use in III-V semiconductor devices.

Semiconductor Device Physics and Design teaches readers how to approach device design from the point of view of someone who wants to improve devices and can see the opportunity and challenges. It begins with coverage of basic physics concepts, including the physics behind polar heterostructures and strained heterostructures. The book then details the important devices ranging from p-n diodes to bipolar and field effect devices. By relating device design to device performance and then relating device needs to system use the student can see how device design works in the real world.

A graduate textbook presenting the underlying physics behind devices that drive today's technologies. The book covers important details of structural properties, bandstructure, transport, optical and magnetic properties of semiconductor structures. Effects of low-dimensional physics and strain - two important driving forces in modern device technology - are also discussed. In addition to conventional semiconductor physics the book discusses self-assembled structures, mesoscopic structures and the developing field of spintronics. The book utilizes carefully chosen solved examples to convey important concepts and has over 250 figures and 200 homework exercises. Real-world applications are highlighted throughout the book, stressing the links between physical principles and actual devices. Electronic and Optoelectronic Properties of Semiconductor Structures provides engineering and physics students and practitioners with complete and coherent coverage of key modern semiconductor concepts. A solutions manual and set of viewgraphs for use in lectures are available for instructors, from solutions@cambridge.org.

Semiconductor Materials presents physico-chemical, electronic, electrical, elastic, mechanical, magnetic, optical, and other properties of a vast group of elemental, binary, and ternary inorganic semiconductors and their solid solutions. It also discusses the properties of organic semiconductors. Descriptions are given of the most commonly used semiconductor devices-charge-coupled devices, field-effect transistors, unijunction transistors, thyristors, Zener and avalanche diodes, and photodiodes and lasers. The current trend of transitioning from silicon

technology to gallium arsenide technology in field-effect-based electronic devices is a special feature that is also covered. More than 300 figures and 100 tables highlight discussions in the text, and more than 2,000 references guide you to further sources on specific topics. Semiconductor Materials is a relatively compact book containing vast information on semiconductor material properties. Readers can compare results of the property measurements that have been reported by different authors and critically compare the data using the reference information contained in the book. Engineers who design and improve semiconductor devices, researchers in physics and chemistry, and students of materials science and electronics will find this a valuable guide.

Aimed primarily at the undergraduate students pursuing courses in semiconductor physics and semiconductor devices, this text emphasizes the physical understanding of the underlying principles of the subject. Since engineers use semiconductor devices as circuit elements, device models commonly used in the circuit simulators, e.g. SPICE, have been discussed in detail. Advanced topics such as lasers, heterojunction bipolar transistors, second order effects in BJTs, and MOSFETs are also covered. With such in-depth coverage and a practical approach, practising engineers and PG students can also use this book as a ready reference.

This book will guide Photovoltaics researchers in a new way of thinking about harvesting light energy from all wavelengths of the solar spectrum. It closes the gap between general solar cells books and photovoltaics journal articles, by focusing on the latest developments in our understanding of solid-state device physics. The material presented is experimental and based on II-VI thin-film materials, mainly CdTe-based solar cells. The authors describe the use of new device design, based on multilayer graded bandgap configuration, using CdTe-based solar cells. The authors also explain how the photo-generated currents can be enhanced using multi-step charge carrier production. The possibility of fabricating these devices using low-cost and scalable electroplating is demonstrated. The value of electroplating for large area electronic devices such as PV solar panels, display devices and nano-technology devices are also demonstrated. By enabling new understanding of the engineering of electroplated semiconductor materials and providing an overview of the semiconductor physics and technology, this practical book is ideal to guide researchers, engineers, and manufacturers on future solar cell device designs and fabrications. Discusses in detail the processes of growths, treatments, solar cell device fabrication and solid state physics, improving readers' understanding of fundamental solid state physics; Enables future improvements in CdTe-based device efficiency; Explains the significance of defects in deposited semiconductor materials and interfaces that affect the material properties and resulting device performance.

Semiconductor Devices: Physics and Technology, Third Edition is an introduction to the physical principles of modern semiconductor devices and their advanced fabrication technology. It begins with a brief historical review of major devices and key technologies and is then divided into three sections: semiconductor material properties, physics of semiconductor devices and processing technology to fabricate these semiconductor devices.

Technology computer-aided design, or TCAD, is critical to today's semiconductor technology and anybody working in this industry needs to know something about TCAD. This book is about how to use computer software to manufacture and test virtually semiconductor devices in 3D. It brings to life the topic of semiconductor device physics, with a hands-on, tutorial approach that de-emphasizes abstract physics and equations and emphasizes real practice and extensive illustrations. Coverage includes a comprehensive library of devices, representing the state of the art technology, such as SuperJunction LDMOS, GaN LED devices, etc.

The new edition of the most detailed and comprehensive single-volume reference on major semiconductor devices The Fourth Edition of Physics of Semiconductor Devices remains the standard reference work on the fundamental physics and operational characteristics of all

major bipolar, unipolar, special microwave, and optoelectronic devices. This fully updated and expanded edition includes approximately 1,000 references to original research papers and review articles, more than 650 high-quality technical illustrations, and over two dozen tables of material parameters. Divided into five parts, the text first provides a summary of semiconductor properties, covering energy band, carrier concentration, and transport properties. The second part surveys the basic building blocks of semiconductor devices, including p-n junctions, metal-semiconductor contacts, and metal-insulator-semiconductor (MIS) capacitors. Part III examines bipolar transistors, MOSFETs (MOS field-effect transistors), and other field-effect transistors such as JFETs (junction field-effect-transistors) and MESFETs (metal-semiconductor field-effect transistors). Part IV focuses on negative-resistance and power devices. The book concludes with coverage of photonic devices and sensors, including light-emitting diodes (LEDs), solar cells, and various photodetectors and semiconductor sensors. This classic volume, the standard textbook and reference in the field of semiconductor devices: Provides the practical foundation necessary for understanding the devices currently in use and evaluating the performance and limitations of future devices Offers completely updated and revised information that reflects advances in device concepts, performance, and application Features discussions of topics of contemporary interest, such as applications of photonic devices that convert optical energy to electric energy Includes numerous problem sets, real-world examples, tables, figures, and illustrations; several useful appendices; and a detailed solutions manual Explores new work on leading-edge technologies such as MODFETs, resonant-tunneling diodes, quantum-cascade lasers, single-electron transistors, real-space-transfer devices, and MOS-controlled thyristors Physics of Semiconductor Devices, Fourth Edition is an indispensable resource for design engineers, research scientists, industrial and electronics engineering managers, and graduate students in the field.

The purpose of this workshop is to spread the vast amount of information available on semiconductor physics to every possible field throughout the scientific community. As a result, the latest findings, research and discoveries can be quickly disseminated. This workshop provides all participating research groups with an excellent platform for interaction and collaboration with other members of their respective scientific community. This workshop's technical sessions include various current and significant topics for applications and scientific developments, including • Optoelectronics • VLSI & ULSI Technology • Photovoltaics • MEMS & Sensors • Device Modeling and Simulation • High Frequency/ Power Devices • Nanotechnology and Emerging Areas • Organic Electronics • Displays and Lighting Many eminent scientists from various national and international organizations are actively participating with their latest research works and also equally supporting this mega event by joining the various organizing committees.

"This book is an introduction to the physical principles of modern semiconductor devices and their advanced fabrication technology. It begins with a brief historical review of major devices and key technologies and is then divided into three sections: semiconductor material properties, physics of semiconductor devices and processing technology to fabricate these semiconductor devices."--Publisher's description.

From physical process to practical applications - Singh makes the complexities of modern semiconductor devices clear! The semiconductor devices that are driving today's information, technologies may seem remarkably complex, but they don't have to be impossible to understand. Filled with figures, flowcharts, and solved examples, Jasprit Singh's Semiconductor Devices provides an accessible, well-balanced introduction to semiconductor physics and its application to modern devices. Beginning with the physical process behind semiconductor devices, Singh clearly explains difficult topics, including bandstructure, effective masses, holes,

doping, carrier transport, and lifetimes. Following these physical fundamentals, you'll explore the operation of important semiconductor devices, such as diodes, transistors, light emitters, and detectors, along with issues relating to the optimization of device performance. Features Over 150 solved examples, integrated throughout the text, clarify difficult concepts. End-of-chapter summary tables and hundreds of figures reinforce the intricacies of modern semiconductor devices. Discussion of device optimization issues explains why you have to trade one performance against another in devices. Shows the relationship of physical parameters to SPICE parameters and its impact on circuit issues. Technology Roadmaps outline what's currently happening in the field and present a look at where device technology is headed in the future. A Bit of History sections, included in each chapter, explore the history of the concepts developed and provide a snapshot of the personalities involved and the challenges of the time.

Physics of Semiconductor Devices covers both basic classic topics such as energy band theory and the gradual-channel model of the MOSFET as well as advanced concepts and devices such as MOSFET short-channel effects, low-dimensional devices and single-electron transistors. Concepts are introduced to the reader in a simple way, often using comparisons to everyday-life experiences such as simple fluid mechanics. They are then explained in depth and mathematical developments are fully described. Physics of Semiconductor Devices contains a list of problems that can be used as homework assignments or can be solved in class to exemplify the theory. Many of these problems make use of Matlab and are aimed at illustrating theoretical concepts in a graphical manner.

An in-depth, up-to-date presentation of the physics and operational principles of all modern semiconductor devices The companion volume to Dr. Sze's classic Physics of Semiconductor Devices, Modern Semiconductor Device Physics covers all the significant advances in the field over the past decade. To provide the most authoritative, state-of-the-art information on this rapidly developing technology, Dr. Sze has gathered the contributions of world-renowned experts in each area. Principal topics include bipolar transistors, compound-semiconductor field-effect-transistors, MOSFET and related devices, power devices, quantum-effect and hot-electron devices, active microwave diodes, high-speed photonic devices, and solar cells. Supported by hundreds of illustrations and references and a problem set at the end of each chapter, Modern Semiconductor Device Physics is the essential text/reference for electrical engineers, physicists, material scientists, and graduate students actively working in microelectronics and related fields.

This text is a first attempt to pull together the whole of semiconductor science and technology since 1970 in so far as semiconductor multilayers are concerned. Material, technology, physics and device issues are described with approximately equal emphasis, and form a single coherent point of view. The subject matter is the concern of over half of today's active semiconductor scientists and technologists, the remainder working on bulk semiconductors and devices. It is now routine to design and the prepare semiconductor multilayers at a time, with independent control over the dropping and composition in each layer. In turn these multilayers can be patterned with features that as a small as a few atomic layers in lateral extent. The resulting structures

open up many new areas of exciting solid state and quantum physics. They have also led to whole new generations of electronic and optoelectronic devices whose superior performance relates back to the multilayer structures. The principles established in the field have several decades to go, advancing towards the ultimate of materials engineering, the design and preparation of solids atom by atom. The book should appeal equally to physicists, electronic engineers and materials scientists.

This new and exciting interactive resource centers around fourteen high quality computer simulations covering essential topics in solid state physics, at advanced undergraduate or graduate level. The computer simulations provided on CD-ROM cover x-ray diffraction, phonons, electron states and dynamics, semiconductors, magnetism, and dislocations. Users can vary different characteristics and immediately see the results in animations and graphical displays. See <http://www.ruph.cornell.edu/sss/sss.html> for example simulations. The companion book is essential for effective use of the simulations. It guides the user through hundreds of exercises and examples, illustrates fundamental physical principles, and contains notes on the relevant physics. The hardcover edition includes the simulations on CD-ROM and a licence for use on a local area network on a single geographical site. The paperback edition (without CD-ROM) is intended for students who have access to the simulations on a local area network.

Halbleiter-Leistungsbaulemente sind das Kernstück der Leistungselektronik. Sie bestimmen die Leistungsfähigkeit und machen neuartige und verlustarme Schaltungen erst möglich. In dem Band wird neben den Halbleiter-Leistungsbaulementen selbst auch die Aufbau- und Verbindungstechnik behandelt: von den physikalischen Grundlagen und der Herstellungstechnologie über einzelne Bauelemente bis zu thermomechanischen Problemen, Zerstörungsmechanismen und Störungseffekten. Die 2., überarbeitete Auflage berücksichtigt technische Neuerungen und Entwicklungen.

A comprehensive guide to current techniques, applications, and trends in InP-based technologies. Introducing one of the hottest technologies in the semiconductor industry, this collection of articles by international leading experts covers the state of the art of indium phosphide (InP)-based materials and devices. From current industry practices to cutting-edge developments to promising research trends, each chapter describes a particular aspect of the technology, giving scientists and engineers the necessary information, including physical principles and technical know-how, to design, apply, and troubleshoot these high-performance, low-cost components for diverse systems-TDM and WDM optical systems or microwave and millimeter-wave systems. The advantages and challenges still to overcome of InP-based semiconductors as compared with the more mature GaAs technology are also thoroughly reviewed. Presented in an easy-to-understand tutorial style, with topics cross-referenced between chapters, InP-Based Materials and Devices features more than 1,500 references as well as 365 figures and tables. Key topics include: * Basic materials physics involved in a wide range of InP-based compounds. * Growth of high-purity bulk and heterostructure epitaxy, including MOCVD, MBE, and GS-MBE. * Hetero-interface control and dry process techniques for device fabrication. * High-performance heterojunction-FETs and HEMTs as well as HBTs for high-speed IC and MMIC applications. * Lasers, amplifiers, and modulators as well as photodiodes and receivers for high-speed and WDM networks. * Optoelectronic integration and packing for functional, low-cost modules.

The Third Edition of the standard textbook and reference in the field of semiconductor devices. This classic book has set the standard for advanced study and reference in the semiconductor device field. Now completely updated and reorganized to reflect the tremendous advances in device concepts and performance, this Third Edition remains the most detailed and exhaustive single source of information on the most important semiconductor devices. It gives readers immediate access to detailed descriptions of the underlying physics and performance characteristics of all major bipolar, field-effect, microwave, photonic, and sensor devices. Designed for graduate textbook adoptions and reference needs, this new edition includes: A complete update of the latest developments New devices such as three-dimensional MOSFETs, MODFETs, resonant-tunneling diodes, semiconductor sensors, quantum-cascade lasers, single-electron transistors, real-space transfer devices, and more Materials completely reorganized Problem sets at the end of each chapter All figures reproduced at the highest quality Physics of Semiconductor Devices, Third Edition offers engineers, research scientists, faculty, and students a practical basis for understanding the most important devices in use today and for evaluating future device performance and limitations. A Solutions Manual is available from the editorial department.

This textbook describes the basic physics of semiconductors, including the hierarchy of transport models, and connects the theory with the functioning of actual semiconductor devices. Details are worked out carefully and derived from the basic physical concepts, while keeping the internal coherence of the analysis and explaining the different levels of approximation. Coverage includes the main steps used in the fabrication process of integrated circuits: diffusion, thermal oxidation, epitaxy, and ion implantation. Examples are based on silicon due to its industrial importance. Several chapters are included that provide the reader with the quantum-mechanical concepts necessary for understanding the transport properties of crystals. The behavior of crystals incorporating a position-dependent impurity distribution is described, and the different hierarchical transport models for semiconductor devices are derived (from the Boltzmann transport equation to the hydrodynamic and drift-diffusion models). The transport models are then applied to a detailed description of the main semiconductor-device architectures (bipolar, MOS, CMOS), including a number of solid-state sensors. The final chapters are devoted to the measuring methods for semiconductor-device parameters, and to a brief illustration of the scaling rules and numerical methods applied to the design of semiconductor devices. The three volumes of this handbook treat the fundamentals, technology and nanotechnology of nitride semiconductors with a clarity and depth not found elsewhere. The handbooks present all the necessary basics of semiconductor and device physics and engineering together with an extensive reference section. They also deal with the properties and processes for thermal, optical (3-, 2-, 1-, 0-dimensional systems), electrical (at low- and high-electric fields, low- and high-magnetic fields for 3- and 2-dimensional systems), magnetism and magnetic properties (in dilute magnetic ion doped compounds) and spin-based device concepts. The associated measurement methods for each material deposition are discussed. The present volume 3 deals with nitride semiconductor devices and device technology. Among the applications areas that feature prominently are LEDs, lasers (including recording), FETs and HBTs (including novel treatment of fundamentals and hot phonon processes affecting the velocity), detectors

and unique issues surrounding solar blind detection. This comprehensive handbook provides all interested researchers and engineers with an accessible treatment of this important class of materials.

Provides a comprehensive treatment of semiconductor device physics and technology, with emphasis on modern planar silicon devices. Physical principles are explained by the use of simple physical models and illustrated by experimental measurements. Semiconductor Physics and Devices brings together the fundamental physics, semiconductor material physics, and semiconductor device physics required to understand semiconductor device characteristics, operation, and limitations. It covers the three basic types of transistors (bipolar, JFET, and MOSFET) and includes discussions about processing techniques such as diffusion and ion implantation. The book features important learning tools such as chapter preview sections, chapter summary and review sections, extensive examples, chapter glossaries, many problems, chapter reading lists, and an appendix with answers to selected problems.

The demand for liquid crystals with better display parameters and lower power consumption has stimulated much research into their properties and characterization. A large team of over 50 leading researchers from the USA, Europe and Japan have focused their expertise to extract and review data on a wide range of properties of nematics, including those which are essential to the development of all types of liquid crystal device. Where appropriate these properties are also explained with expert commentary. The book is fully illustrated and structured for reference.

The advent of the microelectronics technology has made ever-increasing numbers of small devices on a same chip. The rapid emergence of ultra-large-scaled-integrated (ULSI) technology has moved device dimension into the sub-quarter-micron regime and put more than 10 million transistors on a single chip. While traditional closed-form analytical models furnish useful intuition into how semiconductor devices behave, they no longer provide consistently accurate results for all modes of operation of these very small devices. The reason is that, in such devices, various physical mechanisms affect the device performance in a complex manner, and the conventional assumptions (i. e. , one-dimensional treatment, low-level injection, quasi-static approximation, etc.) employed in developing analytical models become questionable. Thus, the use of numerical device simulation becomes important in device modeling. Researchers and engineers will rely even more on device simulation for device design and analysis in the future. This book provides comprehensive coverage of device simulation and analysis for various modern semiconductor devices. It will serve as a reference for researchers, engineers, and students who require in-depth, up-to-date information and understanding of semiconductor device physics and characteristics. The materials of the book are limited to conventional and mainstream semiconductor devices; photonic devices such as light emitting and laser diodes are not included, nor does the book cover device modeling, device fabrication, and circuit applications.

Semiconductor Devices Physics and Technology John Wiley & Sons

The performance of high-speed semiconductor devices—the genius driving digital computers, advanced electronic systems for digital signal processing, telecommunication systems, and optoelectronics—is inextricably linked to the unique physical and electrical properties of gallium arsenide. Once viewed as a novel alternative to silicon, gallium arsenide has swiftly moved into the forefront of the leading high-tech industries as an irreplaceable material in component fabrication. GaAs High-Speed Devices provides a comprehensive, state-of-the-science look at the phenomenally expansive range of engineering devices gallium arsenide has made possible—as well as the fabrication methods, operating principles, device models, novel device designs, and the material properties and physics of GaAs that are so keenly integral to their success. In a clear five-part format, the book systematically examines each of these aspects of GaAs device technology, forming the first authoritative study to consider so many important aspects at once and in such detail. Beginning with chapter 2 of part one, the book discusses such basic subjects as gallium arsenide materials and crystal properties, electron energy band structures, hole and electron transport, crystal growth of GaAs from the melt and defect density analysis. Part two describes the fabrication process of gallium arsenide devices and integrated circuits, shedding light, in chapter 3, on epitaxial growth processes, molecular beam epitaxy, and metal organic chemical vapor deposition techniques. Chapter 4 provides an introduction to wafer cleaning techniques and environment control, wet etching methods and chemicals, and dry etching systems, including reactive ion etching, focused ion beam, and laser assisted methods. Chapter 5 provides a clear overview of photolithography and nonoptical lithography techniques that include electron beam, x-ray, and ion beam lithography systems. The advances in fabrication techniques described in previous chapters necessitate an examination of low-dimension device physics, which is carried on in detail in chapter 6 of part three. Part four includes a discussion of innovative device design and operating principles which deepens and elaborates the ideas introduced in chapter 1. Key areas such as metal-semiconductor contact systems, Schottky Barrier and ohmic contact formation and reliability studies are examined in chapter 7. A detailed discussion of metal semiconductor field-effect transistors, the fabrication technology, and models and parameter extraction for device analyses occurs in chapter 8. The fifth part of the book progresses to an up-to-date discussion of heterostructure field-effect (HEMT in chapter 9), potential-effect (HBT in chapter 10), and quantum-effect devices (chapters 11 and 12), all of which are certain to have a major impact on high-speed integrated circuits and optoelectronic integrated circuit (OEIC) applications. Every facet of GaAs device technology is placed firmly in a historical context, allowing readers to see instantly the significant developmental changes that have shaped it. Featuring a look at devices still under development and device structures not yet found in the literature, GaAs High-Speed Devices also provides a valuable glimpse into the newest innovations at the center of the latest GaAs technology. An essential text for electrical engineers, materials scientists, physicists, and

students, GaAs High-Speed Devices offers the first comprehensive and up-to-date look at these formidable 21st century tools. The unique physical and electrical properties of gallium arsenide has revolutionized the hardware essential to digital computers, advanced electronic systems for digital signal processing, telecommunication systems, and optoelectronics. GaAs High-Speed Devices provides the first fully comprehensive look at the enormous range of engineering devices gallium arsenide has made possible as well as the backbone of the technology—ication methods, operating principles, and the materials properties and physics of GaAs—device models and novel device designs. Featuring a clear, six-part format, the book covers: GaAs materials and crystal properties Fabrication processes of GaAs devices and integrated circuits Electron beam, x-ray, and ion beam lithography systems Metal-semiconductor contact systems Heterostructure field-effect, potential-effect, and quantum-effect devices GaAs Microwave Monolithic Integrated Circuits and Digital Integrated Circuits In addition, this comprehensive volume places every facet of the technology in an historical context and gives readers an unusual glimpse at devices still under development and device structures not yet found in the literature.

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